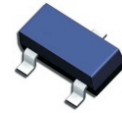


CDST226-G

RoHS Device



Features

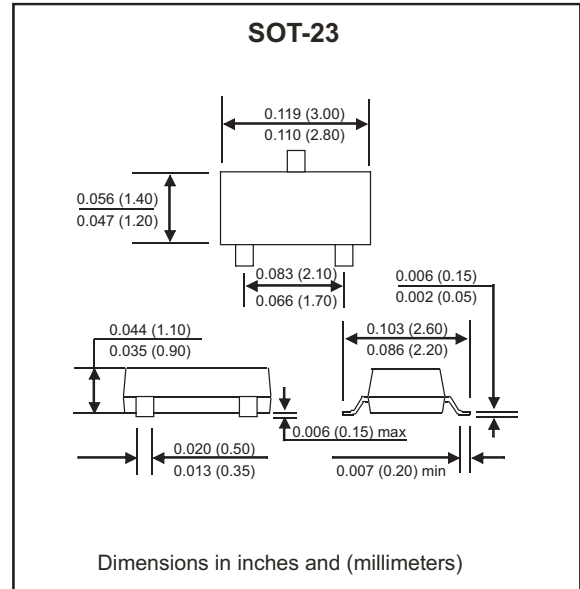
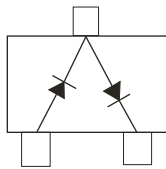
-Power dissipation: 150mW (@ $T_A=25$ °C)

Mechanical data

-Case: SOT-23

-Terminals: Solder plated, solderable per MIL-STD-750, Method 2026.

-Marking: C3



Maximum Rating (at $T_a=25^\circ\text{C}$ unless otherwise noted)

Parameter	Symbol	Limits	Unit
Non-Repetitive peak reverse voltage	V_{RM}	85	V
Peak repetitive peak reverse voltage	V_{RRM}	80	V
Working peak reverse voltage	V_{RWM}		
DC blocking voltage	V_R		
Forward continuous current	I_{FM}	300	mA
Average rectified output current	I_o	100	mA
Peak forward surge current @10mS	I_{FSM}	2	A
Power dissipation	P_D	150	mW
Storage temperature range	T_{STG}	-55 ~ +125	°C

Electrical Characteristics (at $T_a=25^\circ\text{C}$ unless otherwise noted)

Parameter	Symbol	Test Conditions	Min	Max	Unit
Reverse breakdown voltage	V_{BR}	$I_R=100\mu\text{A}$	80		V
Reverse leakage current	I_R	$V_R=80\text{V}$		0.5	μA
Forward voltage	V_F	$I_F=100\text{mA}$		1.2	V
Diode capacitance	C_T	$V_R=0\text{V}$, $f=1\text{MHz}$		3	pF
Reverse recovery time	t_{rr}			4	nS

Electrical and Characteristic Curves (CDST226-G)

Fig.1 - Forward Characteristics

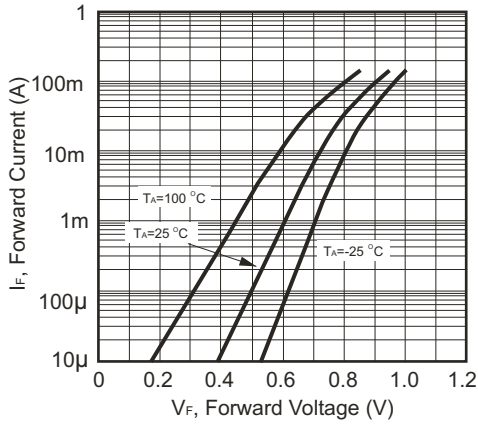


Fig.2 - Reverse Characteristics

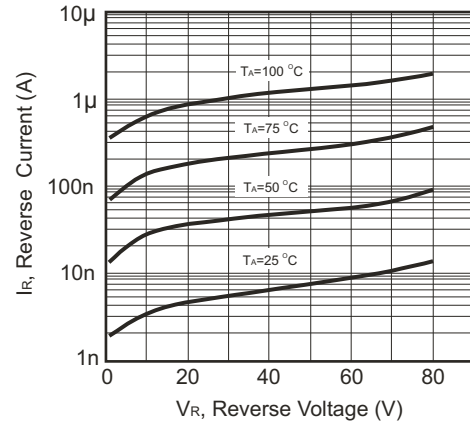


Fig.3 - Diode Capacitance

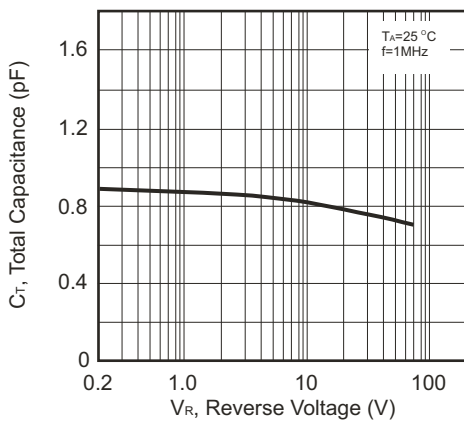


Fig.4 - Reverse Recovery Characteristics

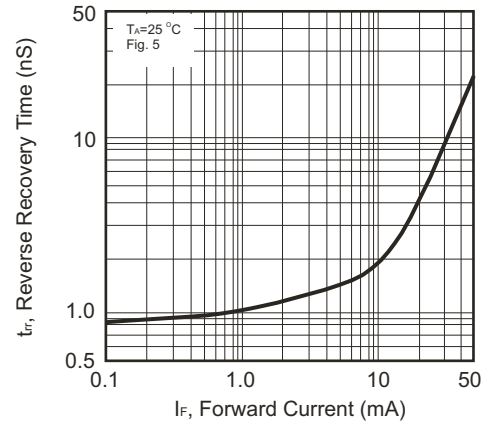


Fig.5 - Reverse Recovery Time (t_{rr}) Test Circuit

